LLDB3/ LLDB4

MINI MELF Glass-Encapsulate Diodes

Silicon bidirectional diac

Features

●VBO 28V-45V

MINI MELF(SOD-80/ LL- 34)

Limiting Values (Absolute Maximum Rating)

PARAMETERS	SYMBOL	VALUE	UNITS
		LLDB3 / LLDB4	
Power Dissipation on Printed Cir cuit(L=10mm) T_A=50℃	Pc	150	mW
Repetitive Peak on-state Current Tp=10uS f=100Hz	I_{TRM}	2.0	A
Storage and Operating Juntion Temperature	T_{STG}/T_J	-40 to +125	℃

Electrical Characteristics (T_a=25℃ Unless otherwise specified）

PAPRAMETERS	SYMBOLS	TEST CONDITIONS		VALUE		UNITS
				LLDB3	LLDB4	
Breakover Voltage*	V_{BO}	C=22nf** See Diagram 1	Min	28	35	V
			Typ	32	45	
			Max	36	45	
Breakover Voltage Symmetry	1+V_{BO}I- 1-V_{BO}I	C=22nf** See Diagram 1	Max	±3		V
Dynamic Breakover Voltage	1±△V1	△I=(I_{BO} to IF=10mA) See FIG 1	Min	5		V
Output Voltage*	V_O	See FIG 2	Min	5		V
Breakover Current*	I_{BO}	C=22nf**	Max	100		uA
Rise Time*	tr	See FIG 3	Typ	1.5		uS
Leakage Current*	I_B	I_B=0.5 V_{BO} MAX See FIG 3	Max	10		uA

NOTE:* Electrical characteristics applicable in both forward and reverse directions.

** Connected in parallel with the devices.

Typical Characteristics

FIG.1-CURRENT-VOLTAGE CHARACTERISTICS

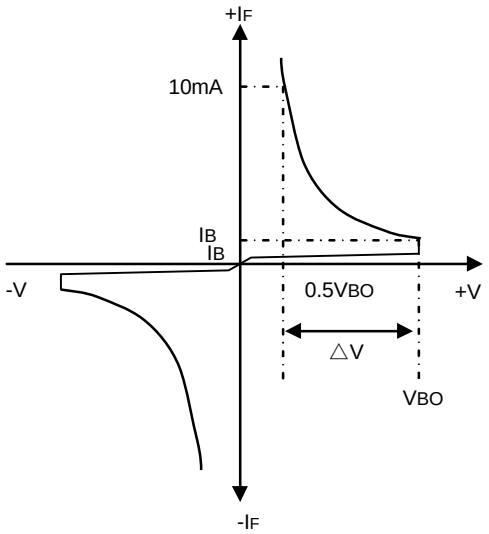


FIG.2-TEST CIRCUIT FOR OUTPUT VOLATGE

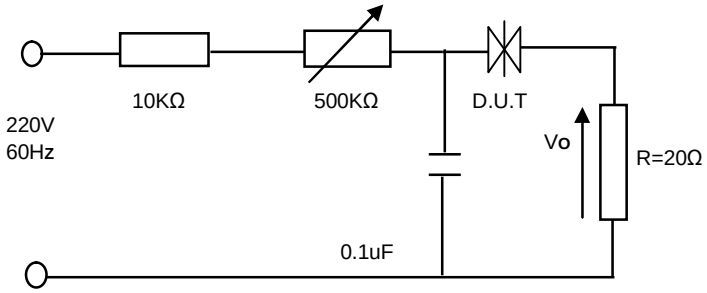


FIG.3-TEST CIRCUIT SEE FIG.2 ADJUST R
FOR Ip=0.5A

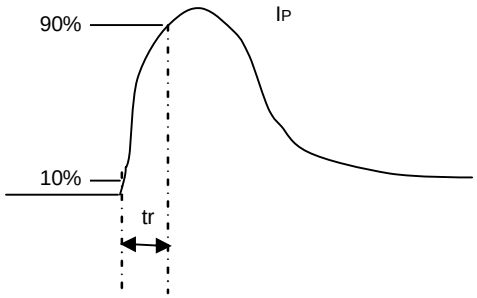


FIG.4-TEST CIRCUIT FOR OUTPUT

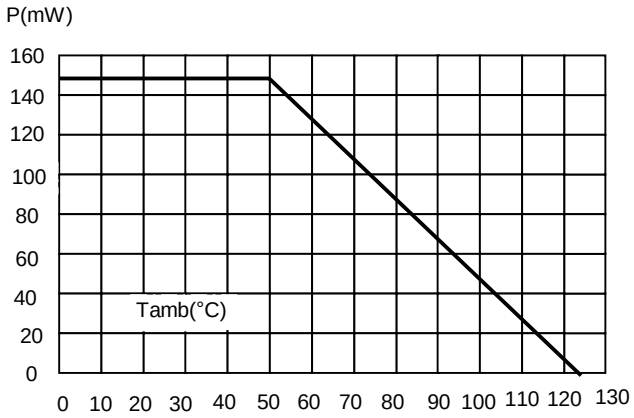


FIG.5-RELATIVE VARIATION OF VBO VERSUS
JUNCTION TEMPERATURE(TYPICAL VALUES)

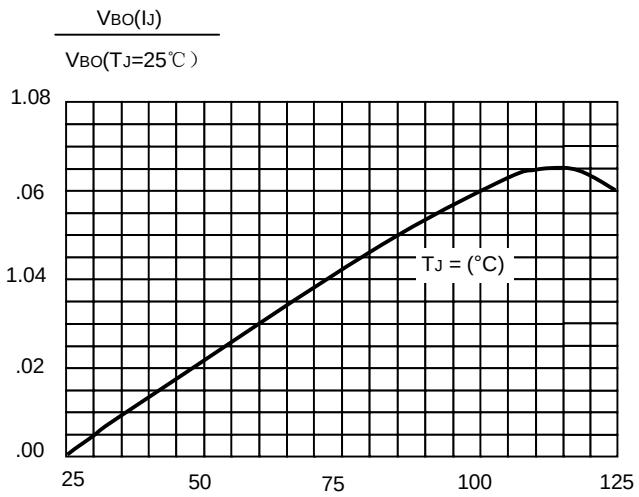
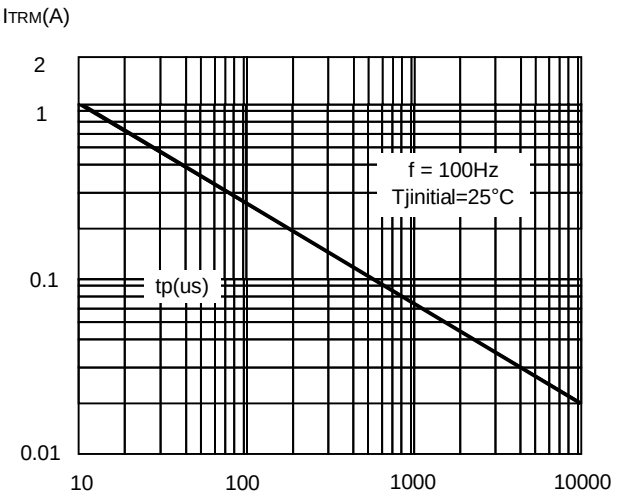
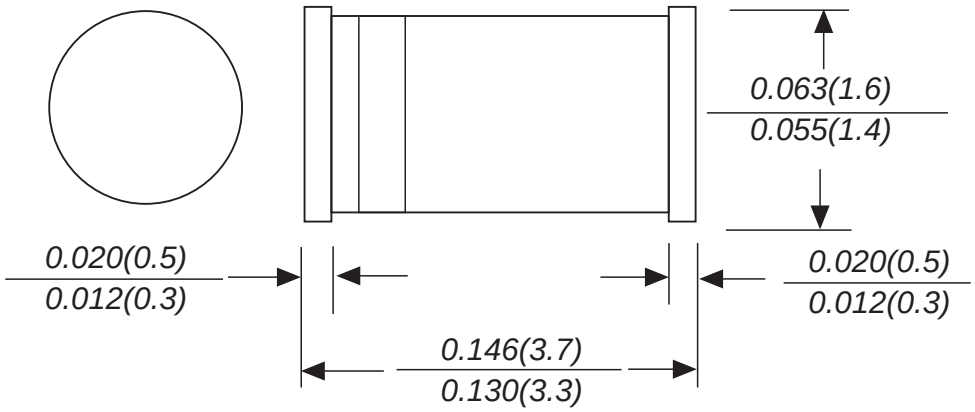


FIG.6-PEAK PULSE CURRENT VERSUS PULSE
DURATION (MAXIMUM VALUES)

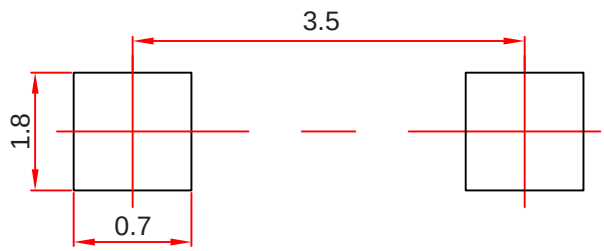


MINI MELF Package Outline Dimensions



Dimensions in millimeters

MINI MELF Suggested Pad Layout



Note:
1.Controlling dimension:in millimeters.
2.General tolerance:± 0.05mm.
3.The pad layout is for reference purposes only.

1. The method of packaging and dimension are shown as below figure. (Dimension in mm)